

HC044N065R4R

650V N-Channel SiC MOSFET

产品特点/Product features

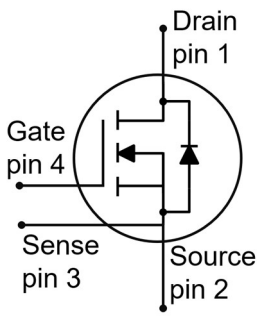
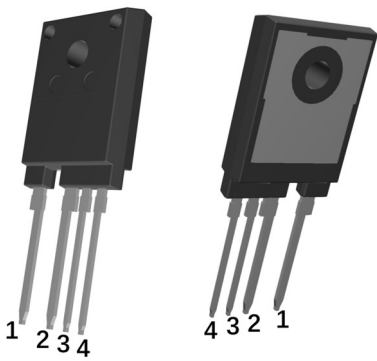
- Kelvin source configuration
开尔文源极配置
- Low specific on-resistance
低导通电阻
- Optimized dynamic performance
优化的动态性能
- Robust gate design
可靠的栅极设计
- 0V turn-off V_{GS} for simple gate driving
0V关断栅源电压，简化栅极驱动
- 100% UIS Tested
100% UIS测试
- Easy to parallel
易于并联

应用领域/Applications

- UPS & Energy storage system
不间断电源（UPS）和储能系统
- Battery formation instrument
电池化成设备
- EV Chargers
电动汽车充电
- Motor Drives
电机驱动

关键性能参数/Key Performance Parameters

Parameter	Value	Unit
V_{DSS}	650	V
$R_{DS(on),typ}$	44	mΩ
$I_{D plus}$	128	A



Type/型号	Package/封装	Marking/标识	Packaging method/包装方式
HC044N065R4R	TO247-4L(HC)	HC044N065R	Tube/管装

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1. Maximum ratings at $T_j = 25^\circ\text{C}$, unless otherwise specified.

最大额定值 默认 $T_j = 25^\circ\text{C}$ 除非另有说明

Table 1 Maximum ratings/最大额定值

Parameter 参数	Symbol 符号	Test conditions 测试条件	Value 值	Unit 单位
Drain-source voltage 漏极-源极电压	V_{DSS}	$T_j \geq 25^\circ\text{C}$	650	V
Drain current ¹ 连续漏极电流	I_{D}	$T_c = 25^\circ\text{C}, V_{\text{GS}} = 18\text{V}$	64	A
		$T_c = 100^\circ\text{C}, V_{\text{GS}} = 18\text{V}$	45	
Peak drain current ² 峰值漏极电流	I_{DM}	$T_c \leq 175^\circ\text{C}$	128	A
Continuous diode current ¹ 连续二极管电流	I_{S}	$T_c = 25^\circ\text{C}, V_{\text{GS}} = -4\text{V}$	47	A
Peak diode current ² 峰值二极管电流	I_{SM}	$T_c = 25^\circ\text{C}, V_{\text{GS}} = -4\text{V}$	128	A
Maximum gate source voltage 栅源最大电压	$V_{\text{GS,MAX}}$		-10~22	V
Recommend gate source voltage 推荐的栅源电压	$V_{\text{GS,op}}$		-4~18	V
Avalanche energy, single pulse 单脉冲雪崩能量	E_{AS}	$I_{\text{AS}} = 15.3\text{A}, V_{\text{DD}} = 100\text{V}, L = 1\text{mH}$	117	mJ
Power dissipation 总耗散功率	P_{tot}	$T_c = 25^\circ\text{C}$	259	W
		$T_c = 100^\circ\text{C}$	129	
Mounting torque 安装扭矩	M_{d}	M3 and M3.5 screw M3或者M3.5螺钉	0.6	Nm

1. Limited by $T_j(\text{max})$ /受限于最大结温

2. Pulse width t_p limited by $T_j(\text{max})$ /脉宽受限于最大结温



2. Thermal characteristics

热特性

Table 2 Thermal characteristics/热特性

Parameter 参数	Symbol 符号	Test conditions 测试条件	Value/值			Unit 单位
			Min.	Typ.	Max.	
Storage Temperature 存储温度	T _{stg}		-55		175	°C
Operating junction Temperature 工作结温	T _j		-55		175	°C
Thermal resistance, junction-case 结-壳热阻	R _{th(j-c)}			0.58		K/W
Thermal resistance, junction-ambient 结-环境热阻	R _{th(j-a)}			40		K/W
Soldering temperature 焊接温度	T _{sold}				260	°C



3. Electrical characteristics at $T_j = 25^\circ\text{C}$, unless otherwise specified.

电气特性 默认 $T_j = 25^\circ\text{C}$ 除非另有说明

Table 3 Static characteristics/静态特性

Parameter 参数	Symbol 符号	Test conditions 测试条件	Value/值			Unit 单位
			Min.	Typ.	Max.	
Drain-source breakdown voltage 漏源击穿电压	$V_{(BR)DSS}$	$I_D = 100\mu\text{A}, V_{GS} = 0\text{V}$	650			V
Gate threshold voltage 门极开启阈值电压	$V_{GS(th)}$	$I_D = 5\text{mA}, V_{DS} = V_{GS}$	$T_j = 25^\circ\text{C}$	1.9	2.6	3.5
			$T_j = 175^\circ\text{C}$		1.9	
Drain-source on-state resistance 漏极-源极导通电阻	$R_{DS(on)}$	$I_D = 20\text{A}, V_{GS(on)} = 15\text{V}$	$T_j = 25^\circ\text{C}$		55	
		$I_D = 20\text{A}, V_{GS(on)} = 18\text{V}$	$T_j = 25^\circ\text{C}$		44	57
			$T_j = 175^\circ\text{C}$		53	
Zero gate voltage drain current 集电极-发射极漏电	I_{DSS}	$V_{DS} = 650\text{V}, V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$		0.1	50
			$T_j = 175^\circ\text{C}$		5	
Gate to source Leakage current 门极-源极漏电流	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = 22\text{V}, T_j = 25^\circ\text{C}$			100	
		$V_{DS} = 0\text{V}, V_{GS} = -10\text{V}, T_j = 25^\circ\text{C}$			100	
Forward transconductance 正向跨导	g_{fs}	$I_D = 20\text{A}, V_{DS} = 20\text{V}$		14		S
Integrated gate resistor 内部门极电阻	R_G	$f = 1\text{MHz}$		1.27		Ω

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Table 4 Dynamic characteristics/动态特性

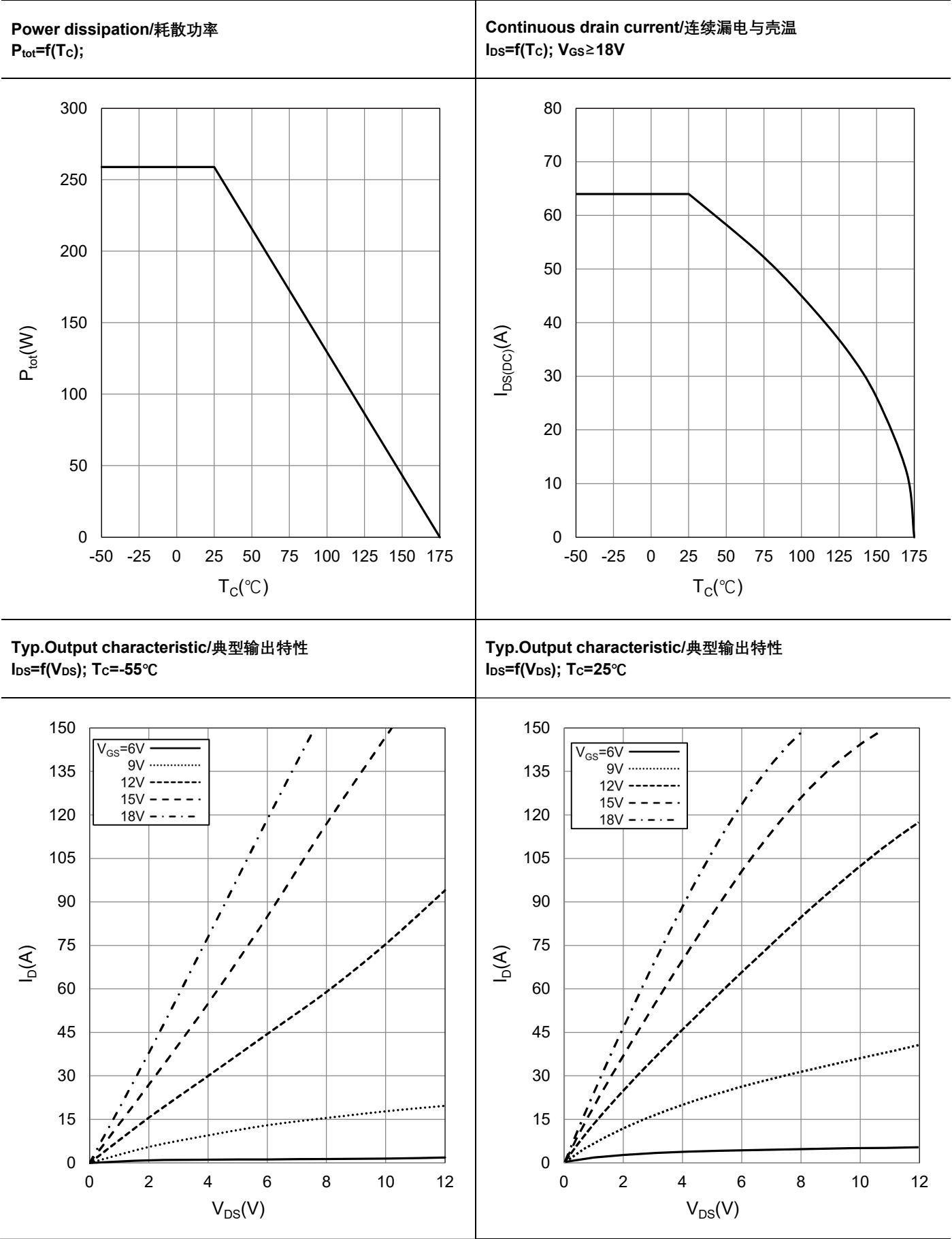
Parameter 参数	Symbol 符号	Test conditions 测试条件	Value/值			Unit 单位
			Min.	Typ.	Max.	
Input capacitance 输入电容	C_{iss}	$V_{DS}=400V$, $V_{GS}=0V$, $f=1MHz$		1376		pF
Output capacitance 输出电容	C_{oss}			119		
Reverse transfer capacitance 反向传输电容	C_{rss}			10		
Coss stored energy 输出电容存储能量	E_{oss}	Calculated based on C_{oss}		9.5		μJ
Total gate charge 总栅极电荷	$Q_{G(tot)}$	$V_{DD}=400V$, $I_D=20A$, $V_{GS}=-4/18V$		59		nC
Gate source charge 栅-源极电荷	Q_{GS}			24		
Gate-drain charge 栅-漏极电荷	Q_{GD}			7.4		
Turn-On Delay Time 开启延迟时间	$t_{d(on)}$	$V_{DD}=400V$, $I_D=10A$, $V_{GS}=-4/18V$, $R_{G(ext)}=5.1\Omega$, $L=300\mu H$		14		ns
Rise time 上升时间	t_r			9		
Turn-Off Delay Time 关闭延迟时间	$t_{d(off)}$			27		
Turn-Off Fall Time 下降时间	t_f			12		
Turn-on switch loss 单次开启损耗	E_{on}			53		μJ
Turn-off switch loss 单次关闭损耗	E_{off}			10		

Table 5 Reverse diode characteristics/体二极管反向特性

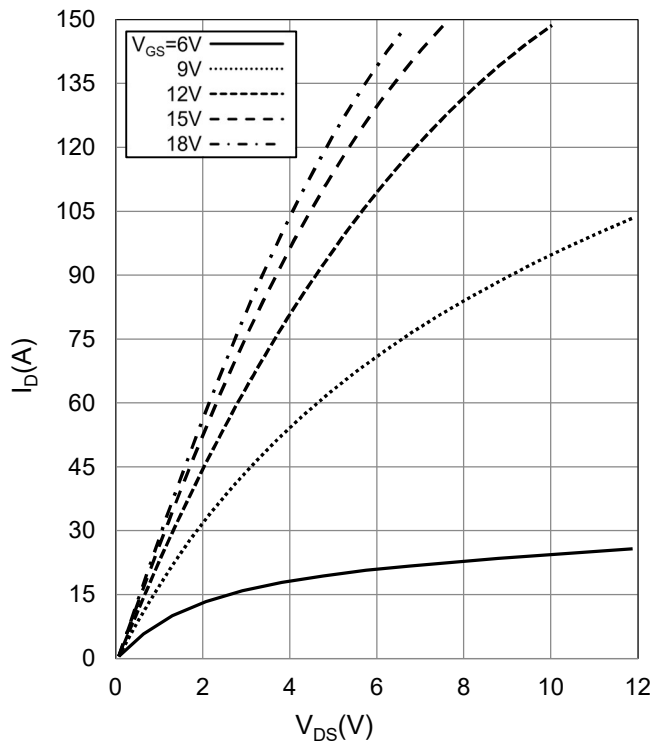
Parameter 参数	Symbol 符号	Test conditions 测试条件	Value/值			Unit 单位
			Min.	Typ.	Max.	
Drain-source reverse voltage 体二极管正向压降	V_{SD}	$I_S=20A, V_{GS}=0V, T_J=25^\circ C$		3.7		V
		$I_S=20A, V_{GS}=-4V, T_J=25^\circ C$		4.2		
		$I_S=20A, V_{GS}=-4V, T_J=175^\circ C$		3.7		
MOSFET forward recovery time MOSFET正向恢复时间	t_{fr}	$V_{DS}=400V$, $I_S=20A$, $-di/dt=500A/\mu s$		25.6		ns
MOSFET forward recovery charge MOSFET正向恢复电荷	Q_{fr}			66.4		nC
MOSFET peak forward recovery current MOSFET正向恢复峰值电流	I_{frm}			5.2		A



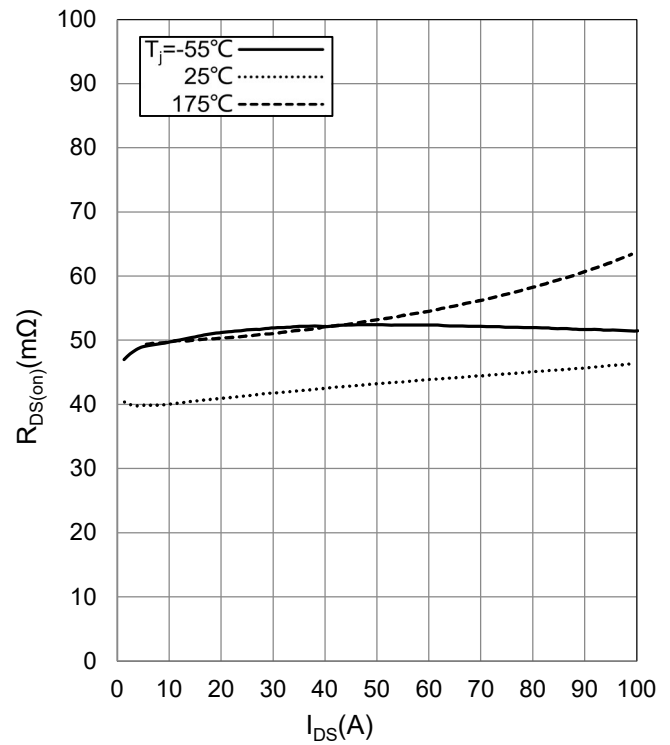
4. Electrical characteristics diagrams
电气特性图表



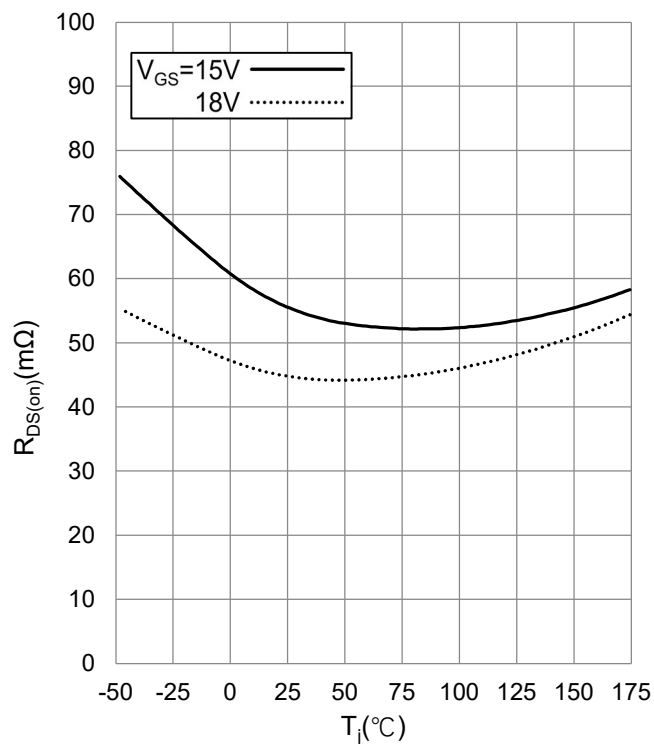
Typ. Output characteristic/典型输出特性
 $I_{DS}=f(V_{DS})$; $T_C=175^\circ\text{C}$



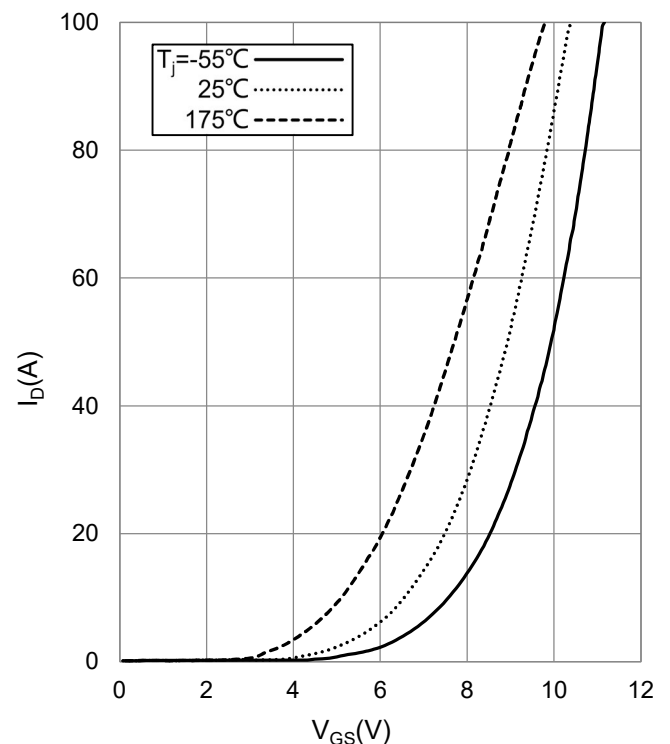
Typ. Drain-source on-state resistance/典型漏源导通电阻
 $R_{DS(on)}=f(I_{DS})$; $V_{GS}=18\text{V}$



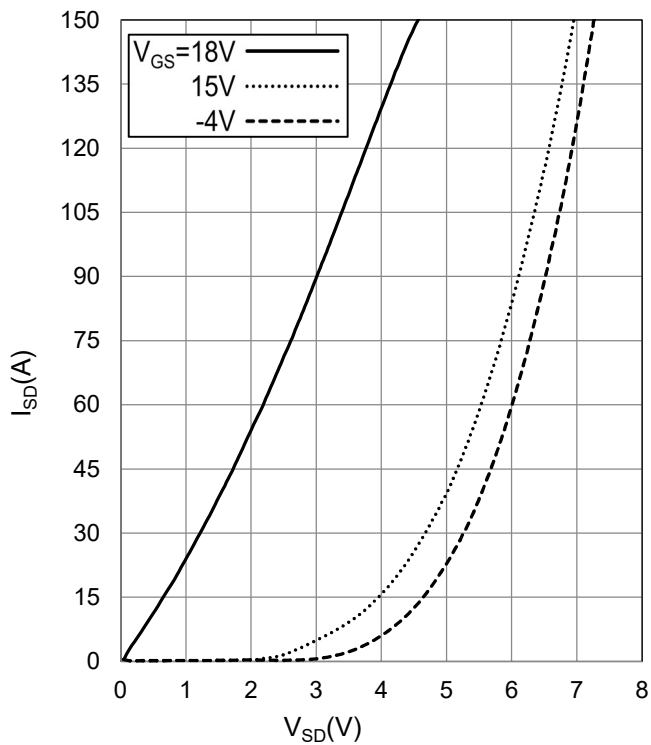
Typ. Drain-source on-state resistance/漏源导通电阻
 $R_{DS(on)}=f(T_j)$; $I_{DS}=20\text{A}$



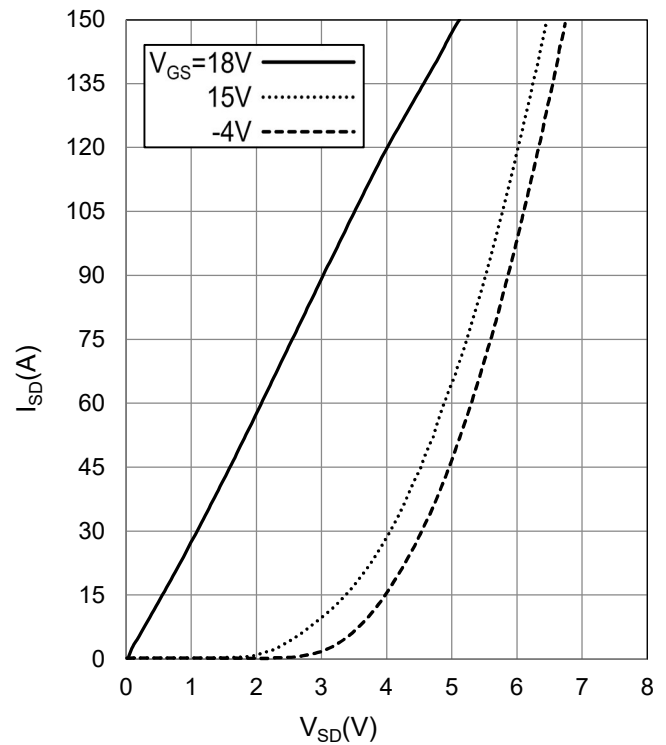
Typ. Transfer characteristics/传输特性
 $I_{DS}=f(V_{GS})$; $V_{DS}=20\text{V}$



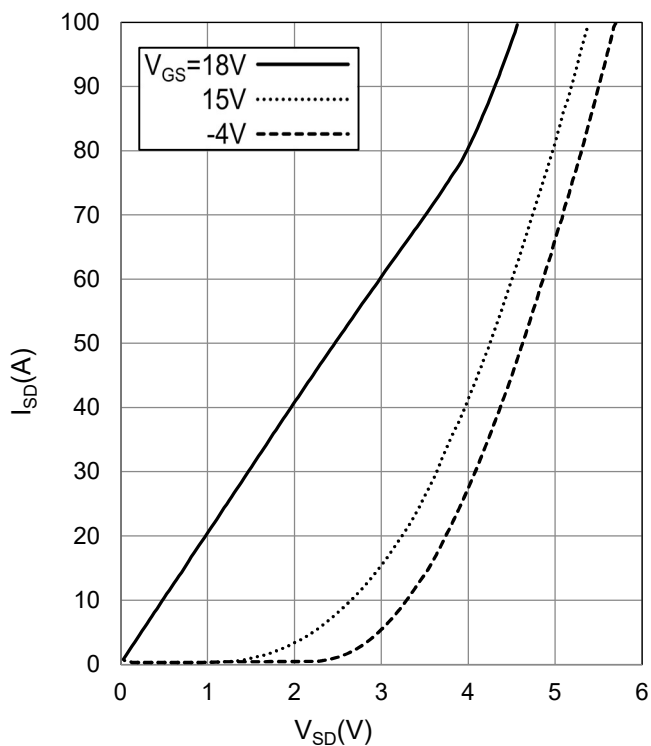
Typ.Reverse drain current characteristics/典型二极管特性
 $I_{SD}=f(V_{SD})$; $T_C=-55^{\circ}\text{C}$



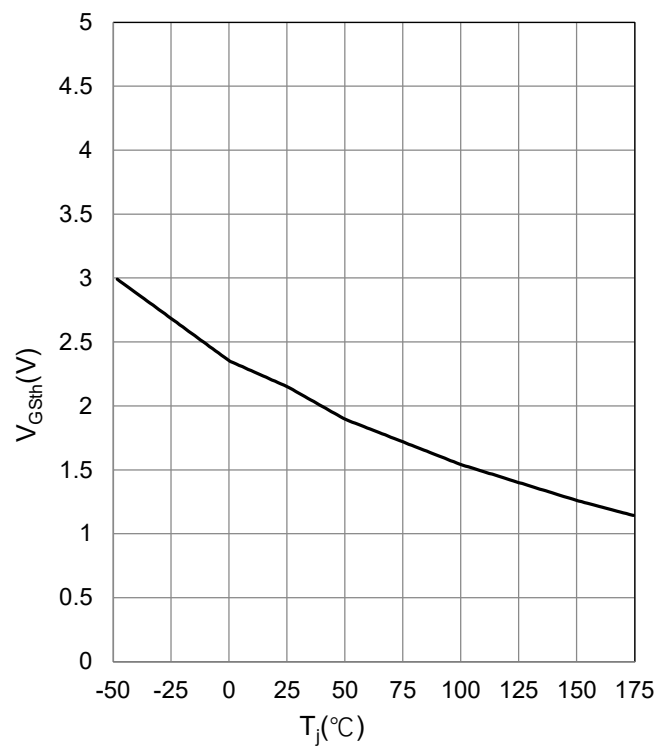
Typ.Reverse drain current characteristics/典型二极管特性
 $I_{SD}=f(V_{SD})$; $T_C=25^{\circ}\text{C}$



Typ.Reverse drain current characteristics/典型二极管特性
 $I_{SD}=f(V_{SD})$; $T_C=175^{\circ}\text{C}$

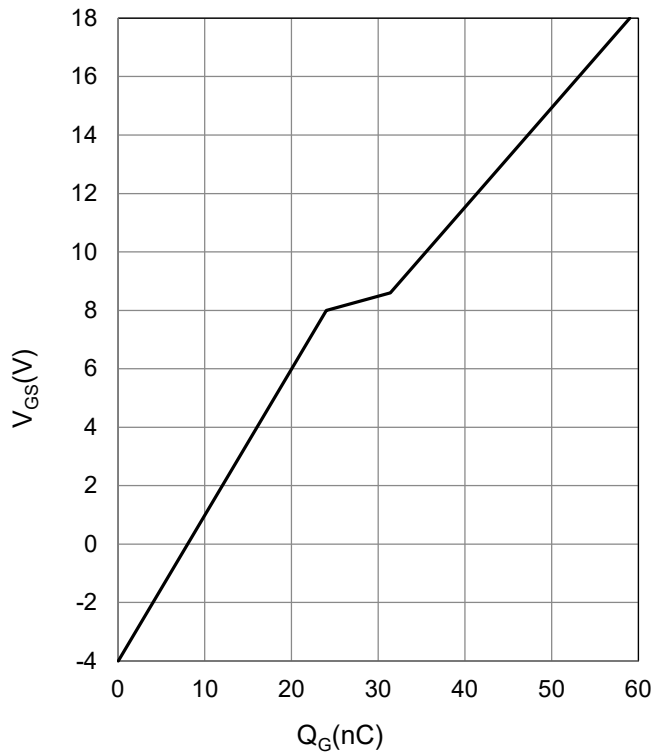


Typ.Gate threshold voltage/门级阈值电压结温特性
 $V_{Gsth}=f(T_j)$; $I_D=5\text{mA}$, $V_{DS}=V_{GS}$



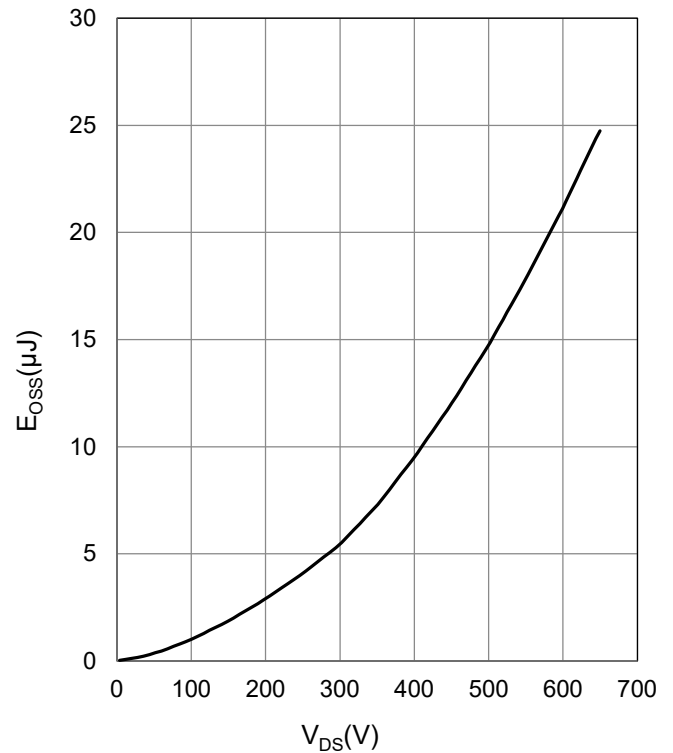
Typ.Gate charge/典型门级电荷

$V_{GS}=f(Q_G)$; $I_{DS}=20A, I_{GS}=0.1mA, V_{DS}=400V$



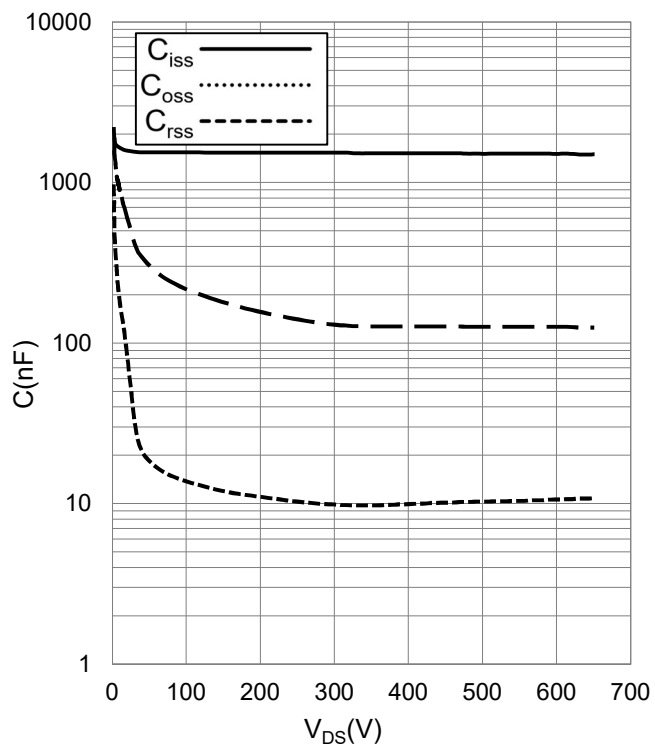
Typ.Coss stored energy/典型Coss存储能量

$E_{oss}=f(V_{DS})$; $T_J=25^\circ C$



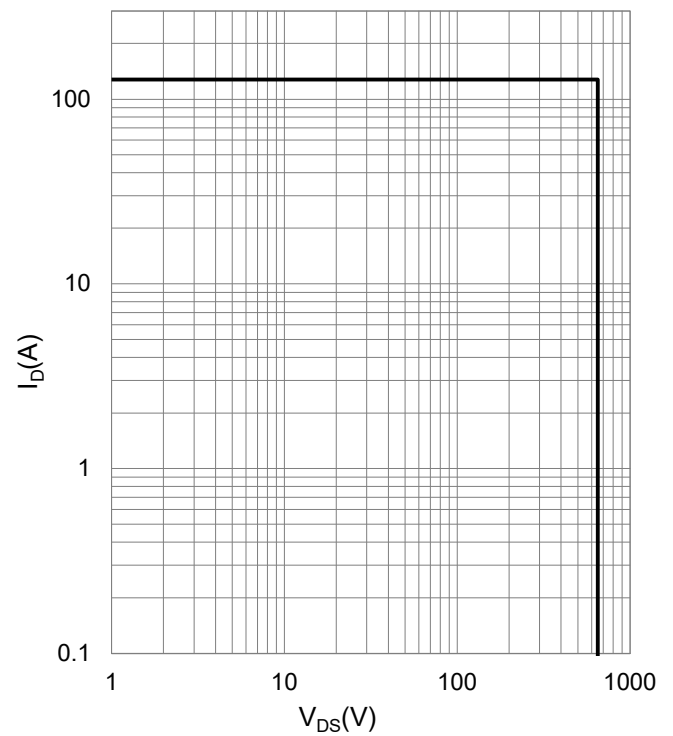
Typ.Capacitances/典型电容特性

$C=f(V_{DS})$; $V_{GS}=0V, T_J=25^\circ C$

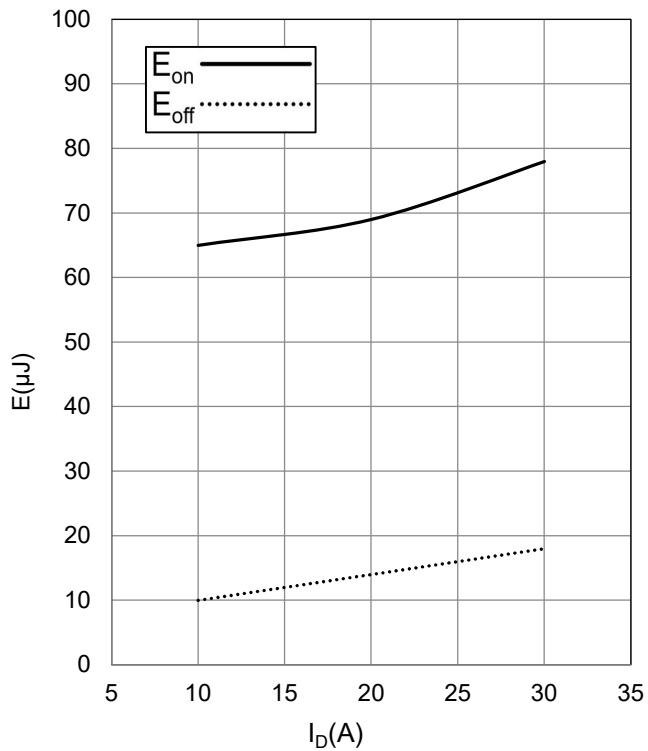


Reverse bias safe operating area/反偏安全工作区

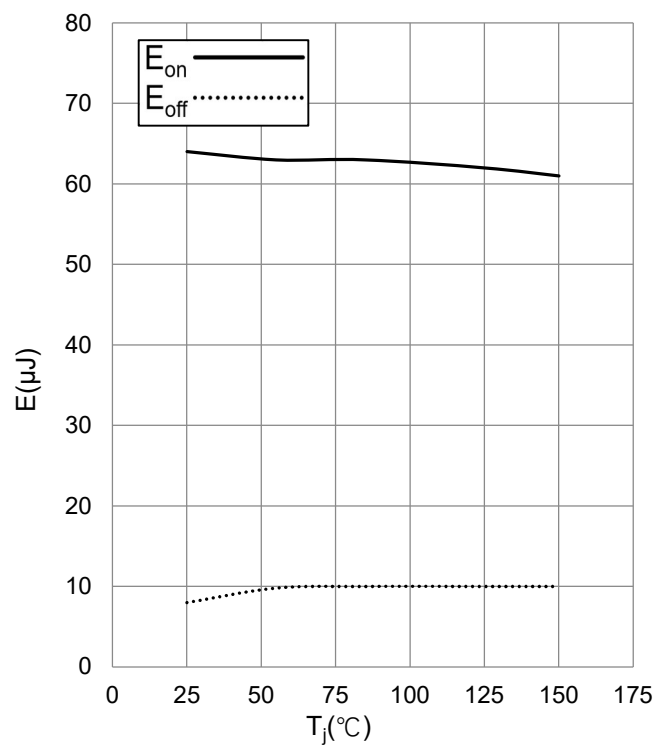
$I_D=f(V_{DS})$; $T_C=25^\circ C, V_{GE}=18V, T_J \leq 175^\circ C$



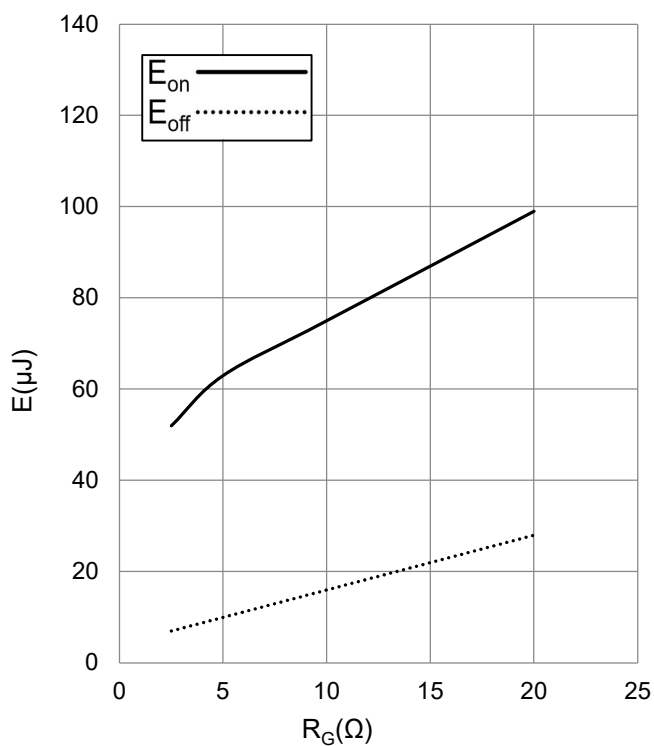
Typ.Switching Losses vs current /动态损耗-电流特性
 $E=f(I_D)$; $V_{GS}=-4/18V$, $R_G=5.1\Omega$, $V_{DD}=400V$, $T_J=25^\circ C$



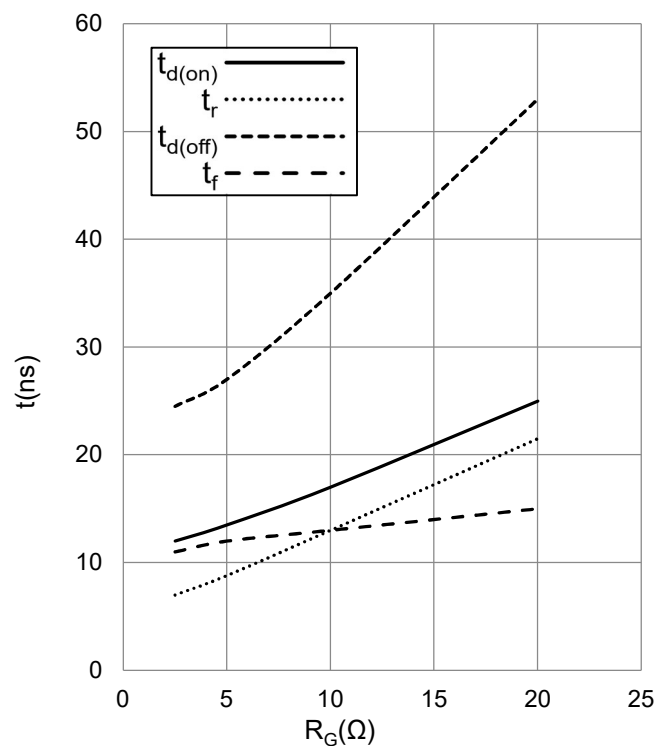
Typ.Switching losses vs temperature/动态损耗-结温特性
 $E=f(T_J)$; $V_{GS}=-4/18V$, $R_G=5.1\Omega$, $V_{DD}=400V$, $I_D=10A$



Typ.Switching losses vs resistance/动态损耗-门级电阻特性
 $E=f(R_G)$; $V_{GS}=-4/18V$, $V_{DD}=400V$, $I_D=10A$, $T_J=25^\circ C$



Typ.Switching times vs resistance/开关时间-门级电阻特性
 $t=f(R_G)$; $V_{GS}=-4/18V$, $V_{DD}=400V$, $I_D=10A$, $T_J=25^\circ C$



封装外形

[illegible]

注：

- Rev.G1.0



6. Revision history

Table 6 Date and version number/日期与版本号

Date日期	Revision版本	Changes更改内容
2025-09-13	Rev.G1.0	Target Datasheet (目标规格书)

7. Matters needing attention

Appendix 1. Important Technical Guidance, Application Policy, and Copyright Notice/重要技术指南、应用规范与版权声明

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